



WBFBP-02C Plastic-Encapsulate Diodes

DS521-30LED02 Schottky Barrier Diode

DESCRIPTION

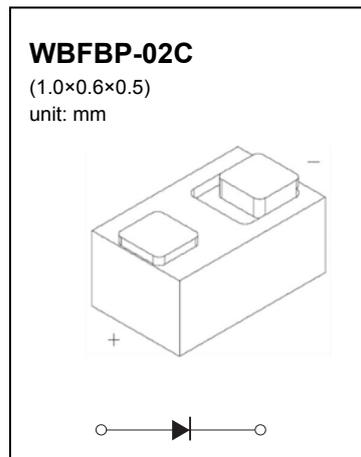
Silicon Epitaxial Planar

FEATURES

- Small surface mounting type
- High reliability

APPLICATION

- High speed switching for detection
- For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM,
- DVD-ROM, Note Book PC, etc.)



MARKING: F



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	100	mA
Peak forward surge current	I_{FSM}	1	A
Power dissipation	P_D	100	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	1000	°C/W
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55~+150	°C

ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse current	I_R	$V_R=10V$			10	μA
Forward voltage	V_F	$I_F=10mA$			0.35	V
		$I_F=100mA$			0.5	